

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
100V	1.6mΩ@10V	260A



合肥矽普半导体

Siliup Semiconductor Technology Co., Ltd

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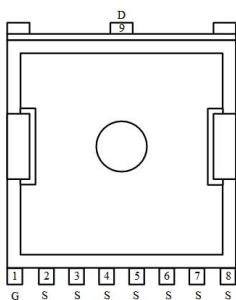
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test

Applications

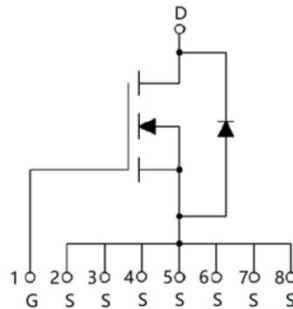
- PWM Application
- Hard switched and high frequency circuits
- Power Management

Package

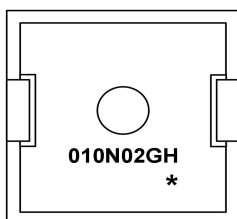


Toll

Circuit diagram



Marking



010N02GH : Product code
* : Month code

Order Information

Device	Package	Unit/Tape
SP010N02GHTO	TOLL	2000

Absolute maximum ratings (Ta=25°C, unless otherwise noted)

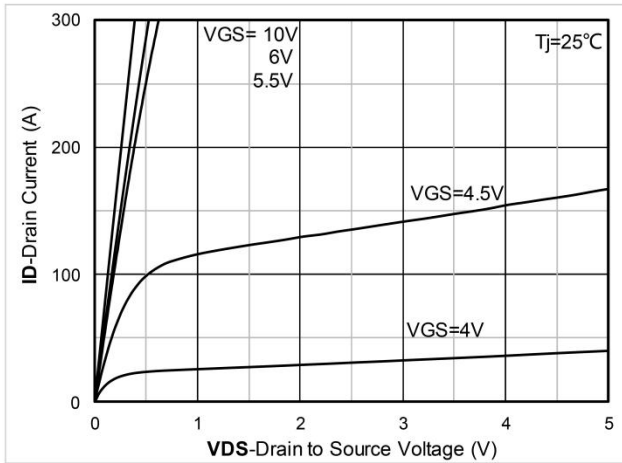
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current1 (Tc=25°C)	I_D	260	A
Continuous Drain Current1 (Tc=100°C)	I_D	175	A
Pulsed Drain Current	I_{DM}	1040	A
Single Pulse Avalanche Energy ¹	E_{AS}	1560	mJ
Power Dissipation (Tc=25°C)	P_D	280	W
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	0.45	°C/W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

Electrical characteristics (Ta=25°C, unless otherwise noted)

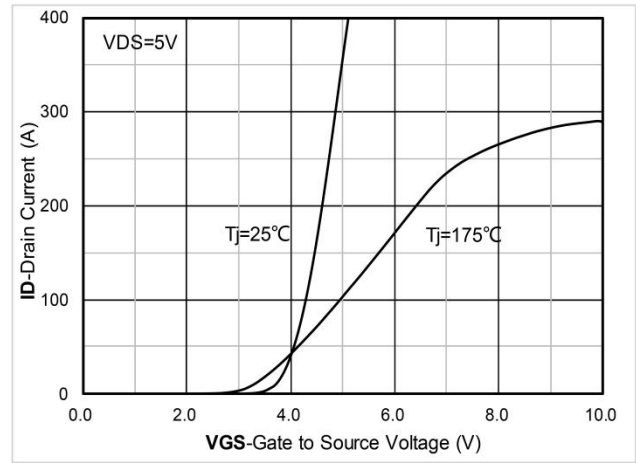
Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$ID = 250\mu A, VGS = 0V$	100	110	-	V
Drain Cut-Off Current	$IDSS$	$VDS = 80V, VGS = 0V$	-	-	1	μA
Gate Leakage Current	$IGSS$	$VGS = \pm 20V, VDS = 0V$	-	-	± 0.1	
Gate Threshold Voltage	$VGS(th)$	$VDS = VGS, ID = 250\mu A$	2.7	3.2	4	V
Drain-Source ON Resistance	$RDS(ON)$	$VGS = 10V, ID = 20A$	-	1.6	2	m Ω
Dynamic Characteristics						
Input Capacitance	$Ciss$	$VDS = 50V, VGS = 0V, f = 1.0MHz$	-	9625	-	pF
Output Capacitance	$Coss$		-	1608	-	
Reverse Transfer Capacitance	$Crss$		-	75	-	
Total Gate Charge	Qg	$VDS = 50V, VGS = 10V, ID = 20A$	-	160	-	nC
Gate-Source Charge	Qgs		-	31	-	
Gate-Drain Charge	Qgd		-	37	-	
Switching Characteristics						
Turn-On Delay Time	$td(on)$	$VGS = 10V, VDS = 50V, RL = 2.5\Omega$ $RG = 6.0\Omega$	-	35	-	nS
Rise Time	tr		-	68	-	
Turn-Off Delay Time	$td(off)$		-	150	-	
Fall Time	tf		-	105	-	
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	VSD	$IS = 1A, VGS = 0V$	-	-	1.2	V
Maximum Body-Diode Continuous Current	IS		-	-	260	A
Reverse Recovery Time	Trr	$TJ = 25^{\circ}C, IF = 100A$ $di/dt = 100A/us$	-	97	-	nS
Reverse Recovery Charge	Qrr		-	228	-	nC

Note :

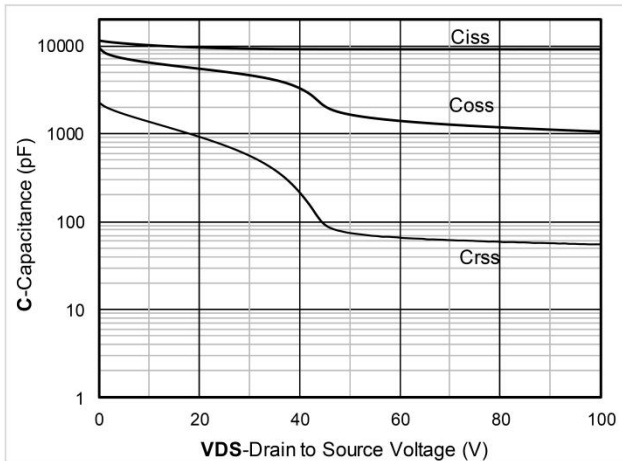
1. The test condition is $V_{DD} = 50V, V_{GS} = 10V, L = 0.5mH, R_G = 25\Omega$

**Typical Characteristics**

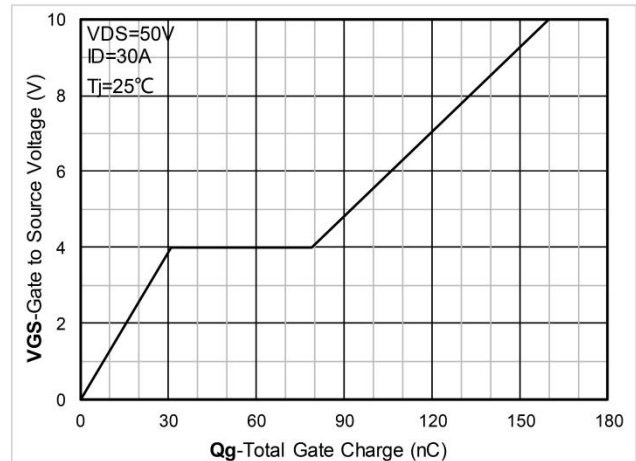
Output Characteristics



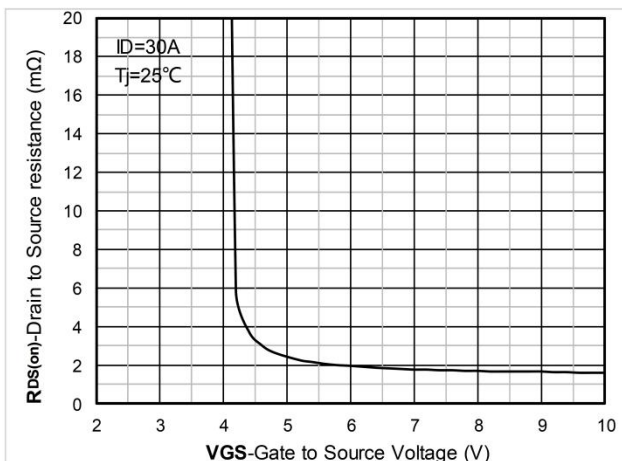
Transfer Characteristics



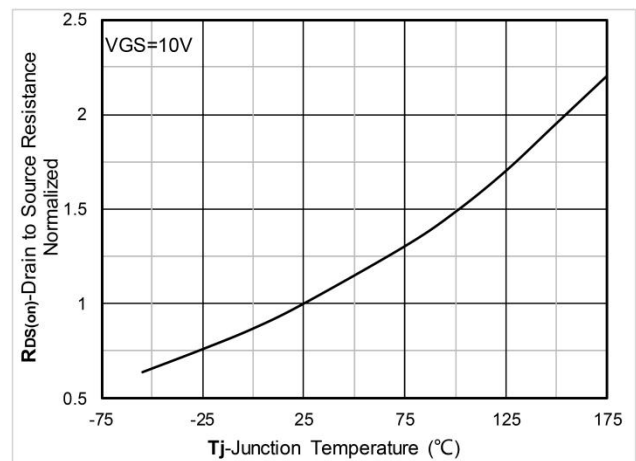
Capacitance Characteristics



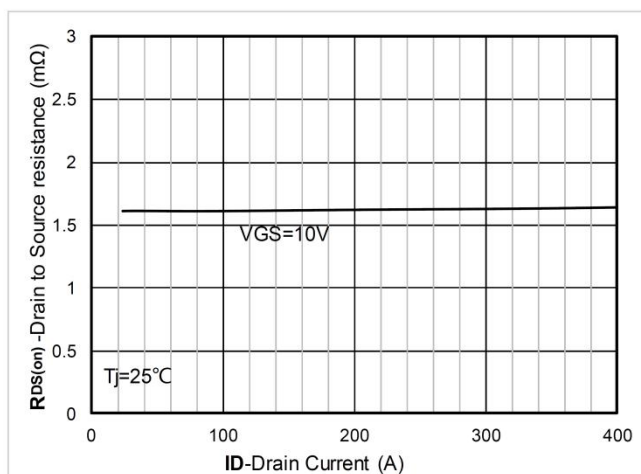
Gate Charge



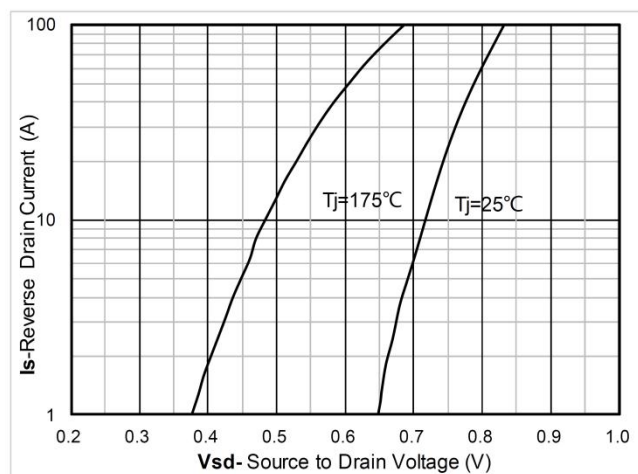
On-Resistance vs Gate to Source Voltage



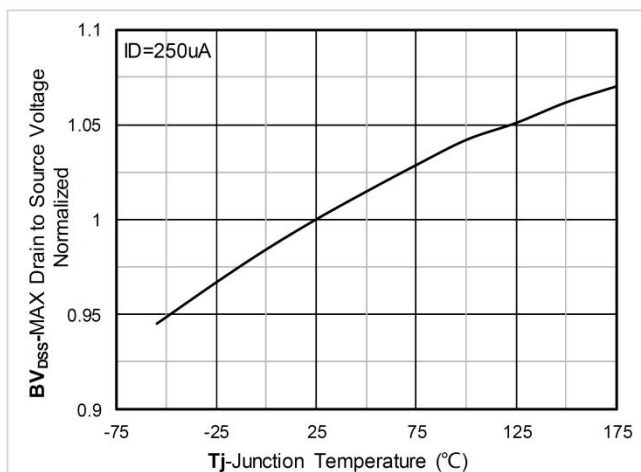
Normalized On-Resistance



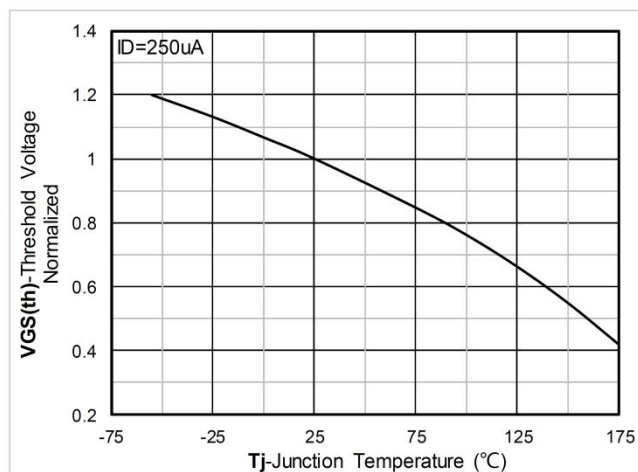
$R_{DS(on)}$ VS Drain Current



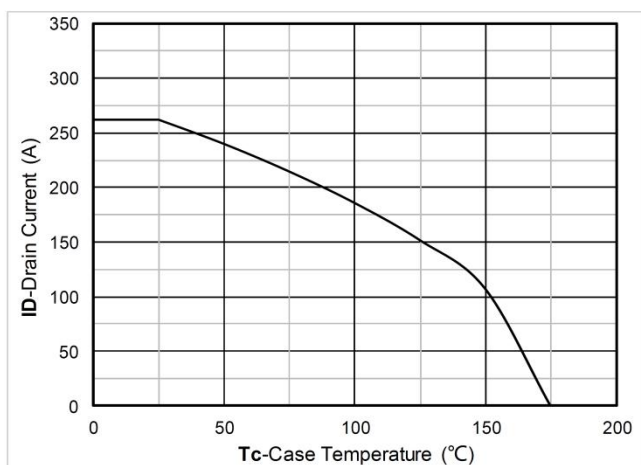
Forward characteristics of reverse diode



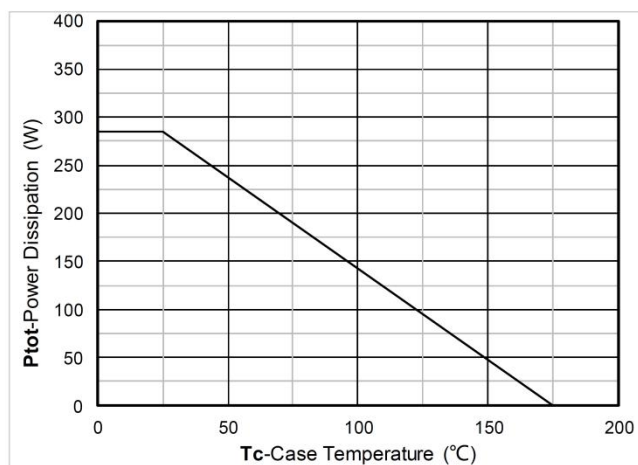
Normalized breakdown voltage



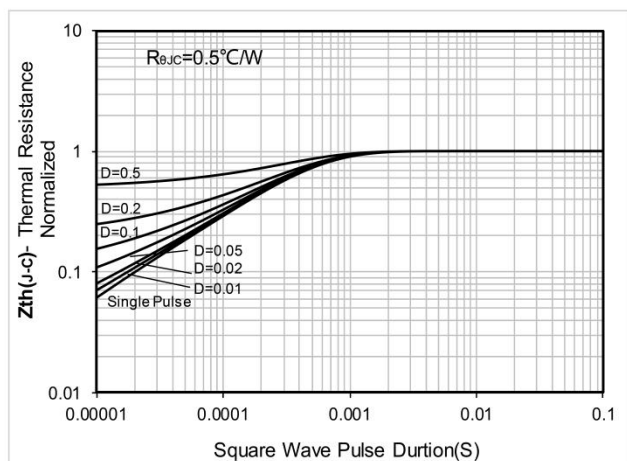
Normalized Threshold voltage



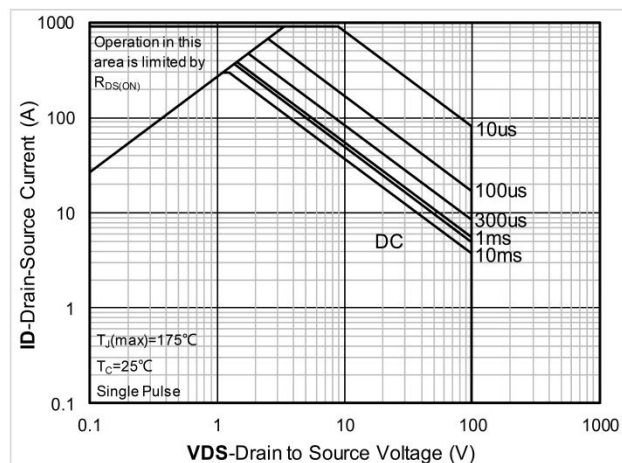
Current dissipation



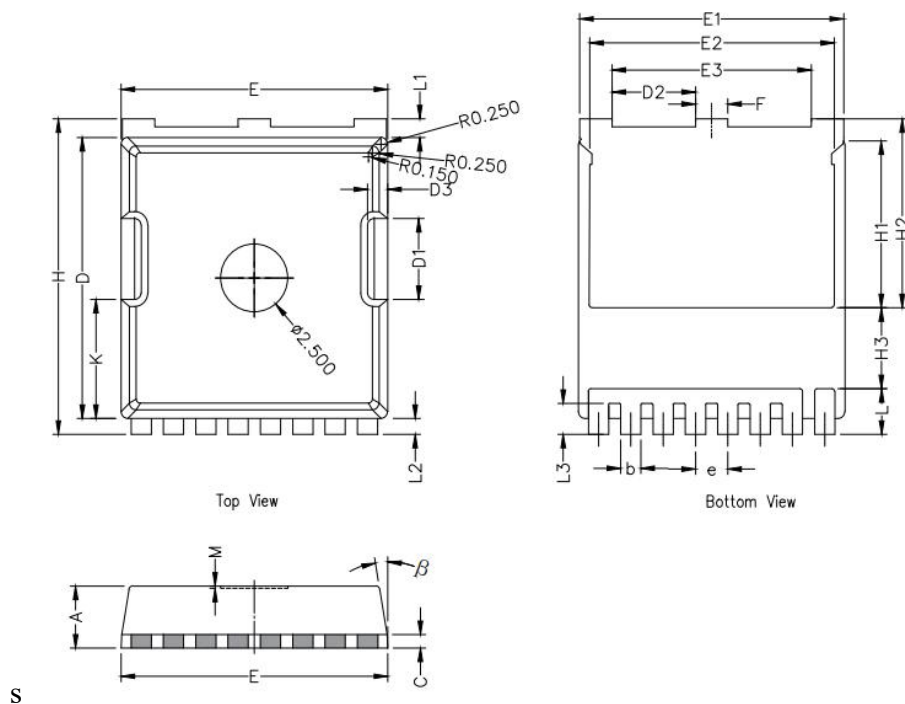
Power dissipation



Maximum Transient Thermal Impedance



Safe Operation Area

**TOLL Package Information**

Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	2.20	2.30	2.40
b	0.65	0.75	0.85
C	0.508 REF		
D	10.25	10.40	10.55
D1	2.85	3.00	3.15
E	9.75	9.90	10.05
E1	9.65	9.80	9.95
E2	8.95	9.10	9.25
E3	7.25	7.40	7.55
e	1.20 BSC		
F	1.05	1.20	1.35
H	11.55	11.70	11.85
H1	6.03	6.18	6.33
H2	6.85	7.00	7.15
H3	3.00 BSC		
L	1.55	1.70	1.85
L1	0.55	0.7	0.85
L2	0.45	0.6	0.75
M	0.08 REF.		
β	8°	10°	12°
K	4.25	4.40	4.55